

MPSA18



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NPN General Purpose Amplifier

This device is designed for low noise, high gain, applications at collector currents from 1 μ A to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	45	V
V_{EBO}	Emitter-Base Voltage	6.5	V
I _C	Collector Current - Continuous	100	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Therm	Thermal Characteristics TA = 25°C unless otherwise noted			
Symbol	Characteristic	Мах	Units	
		MPSA18		
P _D	Total Device Dissipation	625	mW	
	Derate above 25°C	5.0	mW/°C	
$R_{\theta_{JC}}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

NPN General Purpose Amplifie (continued

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	Symbol	Parameter	Test Conditions	Min	Max	Units
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$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	OFF CHA	RACTERISTICS				
	/ _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	45		V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	/ _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	45		V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	/ _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10\mu {\rm A}, I_{\rm C} = 0$	6.5		V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	СВО	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$		50	nA
V _{CE} = 5.0 V, I _C = 1.0 mA 500 V _{CE} = 5.0 V, I _C = 10 mA 500 V _{CE} = 5.0 V, I _C = 10 mA 500 V _{CE} = 5.0 V, I _C = 10 mA 0.2 V _{CE} = 50 mA, I _B = 0.5 mA 0.2 I _C = 50 mA, I _B = 5.0 mA 0.3 V _{EE} = 5.0 V, I _C = 1.0 mA 0.3 V _{BE} (on) Base-Emitter On Voltage V _{CE} = 5.0 V, I _C = 1.0 mA 0.7 SMALL SIGNAL CHARACTERISTICS Cob Collector-Base Capacitance V _{CB} = 5.0 V, f = 1.0 MHz 3.0 PF Cab Emitter-Base Capacitance V _{EB} = 0.5 V, f = 1.0 MHz 6.5 Current Gain - Bandwidth Product I _C = 1.0 mA, V _{CE} = 5.0 V, 100 MF Noise Figure V _{CE} = 5.0 V, I _C = 100 µA, R _S = 10 kΩ, f = 1.0 kHz,						
			$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	500	1500	
W_{BE(OR)}Base-Emitter On Voltage $V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$ 0.7VSMALL SIGNAL CHARACTERISTICS C_{cb} Collector-Base Capacitance $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ 3.0pF C_{eb} Emitter-Base Capacitance $V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ 6.5pF i_T Current Gain - Bandwidth Product $I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, 100$ MHzNFNoise Figure $V_{CE} = 5.0 \text{ V}, I_C = 100 \text{ µA}, R_S = 10 \text{ k}\Omega, f = 1.0 \text{ kHz}, 1.5$ dB	√ _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		0.2	-
SMALL SIGNAL CHARACTERISTICS C_{cb} Collector-Base Capacitance $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ 3.0 pF C_{eb} Emitter-Base Capacitance $V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ 6.5 pF f_T Current Gain - Bandwidth Product $I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz}$ 100 MHz NFNoise Figure $V_{CE} = 5.0 \text{ V}, I_C = 100 \mu \text{A}, R_S = 10 \text{ k}\Omega, f = 1.0 \text{ kHz}, $	V _{BE(On)}	Base-Emitter On Voltage				
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			V _{CB} = 5.0 V, f = 1.0 MHz		3.0	pF
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$					6.5	
$R_{\rm S} = 10 \text{ k}\Omega, \ f = 1.0 \text{ kHz},$		•	I_{C} = 1.0 mA, V_{CE} = 5.0 V,	100		MHz
*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%	NF	Noise Figure			1.5	dB
	*Pulse Test:	Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%				



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